

1N55B
GOLD BONDED GERMANIUM DIODE

FEATURES

Low forward voltage drop—low power consumption
 Thirty years of proven reliability—one million hours mean time between failures (MTBF)
 Very low noise level
 Metallurgically bonded

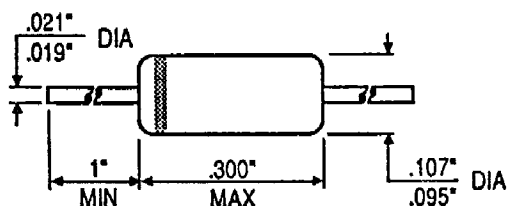
ABSOLUTE MAXIMUM RATINGS (at 25 °C, unless otherwise specified)

Peak Inverse Voltage 190 Volts
 Peak Forward Current 500 mA
 Operating Temperature Range - 65 °C to 85 °C
 Average Power Dissipation 80 mW

ELECTRICAL CHARACTERISTICS

	Symbol	Conditions	Min	Max	Unit	T °C
Peak Inverse Voltage	PIV	1 mA	190		V	25 °C
Reverse Current	I_r	150 V		500	μ A	25 °C
Forward Voltage	V_f	5 mA		1	V	25 °C

MECHANICAL



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